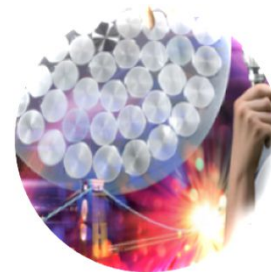


Atomic Layer Deposition (ALD) overview

Oxford Instruments Plasma Technology Gases and precursors



- Cutting edge plasma ALD systems with thermal ALD as standard
- Mixed mode operation within a single recipe
 - No hardware changes required to switch mode between plasma and thermal ALD
 - e.g. for platinum, start with plasma to minimise nucleation delay and continue with thermal



OpAL



FlexAL

- Extensive process capability;
 - Precursor options for research (up to 100g) and production (up to 500g)
 - Up to 8 liquid/solid precursors (3+3+1+1)
 - Up to 10 gas precursors
 - Water and ozone in addition
- Clusterable to PECVD, RIE, sputter modules
- Turbo pump for moisture sensitive nitrides and metals.

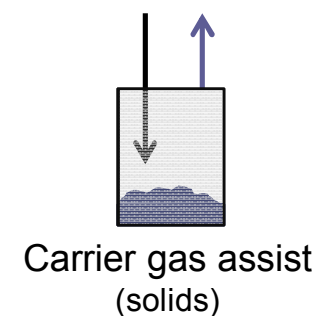
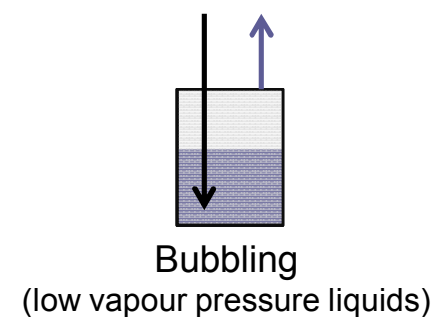
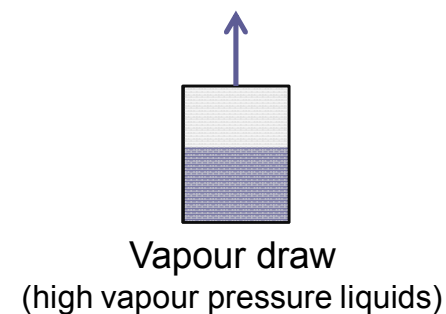


Precursor Delivery Options

- Each module with wide capabilities for;
 - Liquid or solid precursors
 - Temperature range from 30 – 200°C
 - Vapour draw, carrier gas assist or bubbling modes
 - Uses standard canisters from all major precursor suppliers - no need to send a special canister for filling

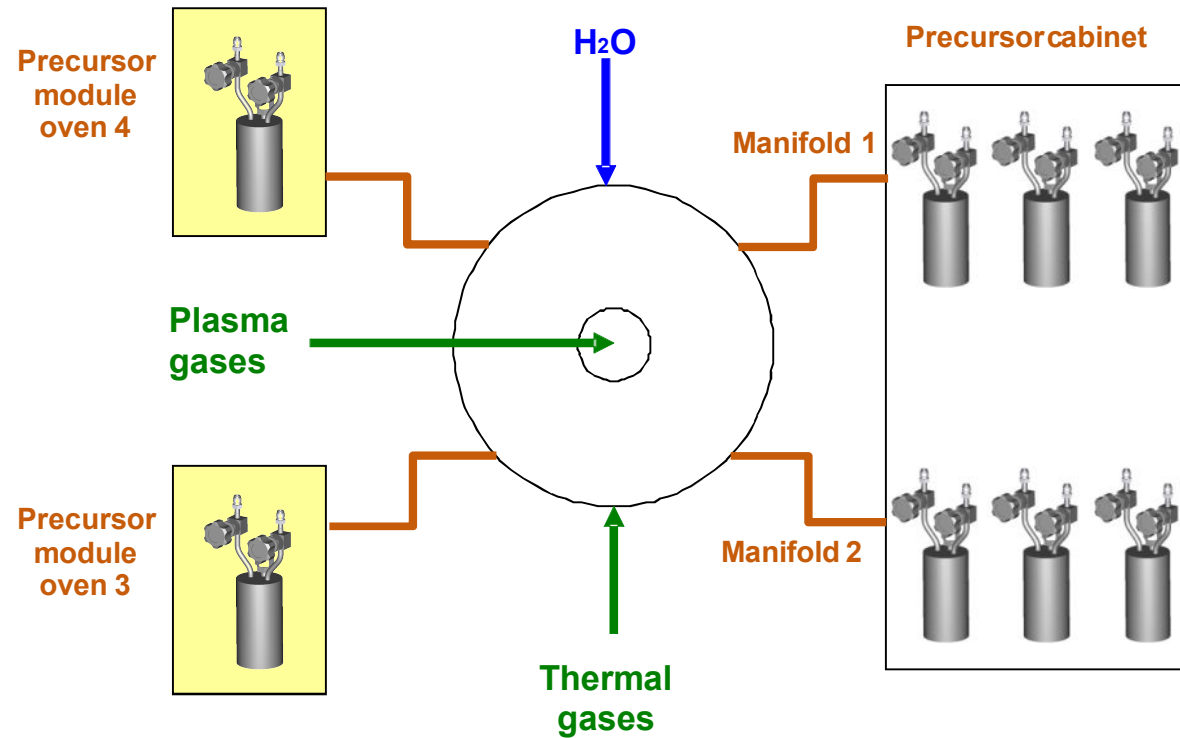


Dip tube



Multiple precursor inputs

- 8 metal liquid or solid rapid bubbled precursors
- 10 plasma and thermal gases
- Water and Ozone delivered separately



Precursor 6-way cabinet

- Extensive process capability
 - Up to 6 liquid/solid precursors on two manifolds
 - Options for up to 100g
- Precise and uniform temperature control with jacket design up to 200°C
- Optimised heated delivery lines up to 200°C



Precursor single cabinet

- When a dedicated manifold is required
 - Highly reactive precursors
 - Development and integration of new precursors
- Uniform precursor temperature control 190°C
 - Allows for heating of irregular shaped ampoules
- Optimised heated delivery lines up to 200°C



Safety Features

- Precursors stored in stainless steel cabinet
- Nitrogen purge and extract to provide low oxygen atmosphere
- Glove panel for use during precursor exchange
- Fully illustrated precursor exchange procedures with check lists
- Remote input to shut down precursors from an external gas detector or extract flow rate monitor



Rapid gas precursor delivery

 Fast ALD valve

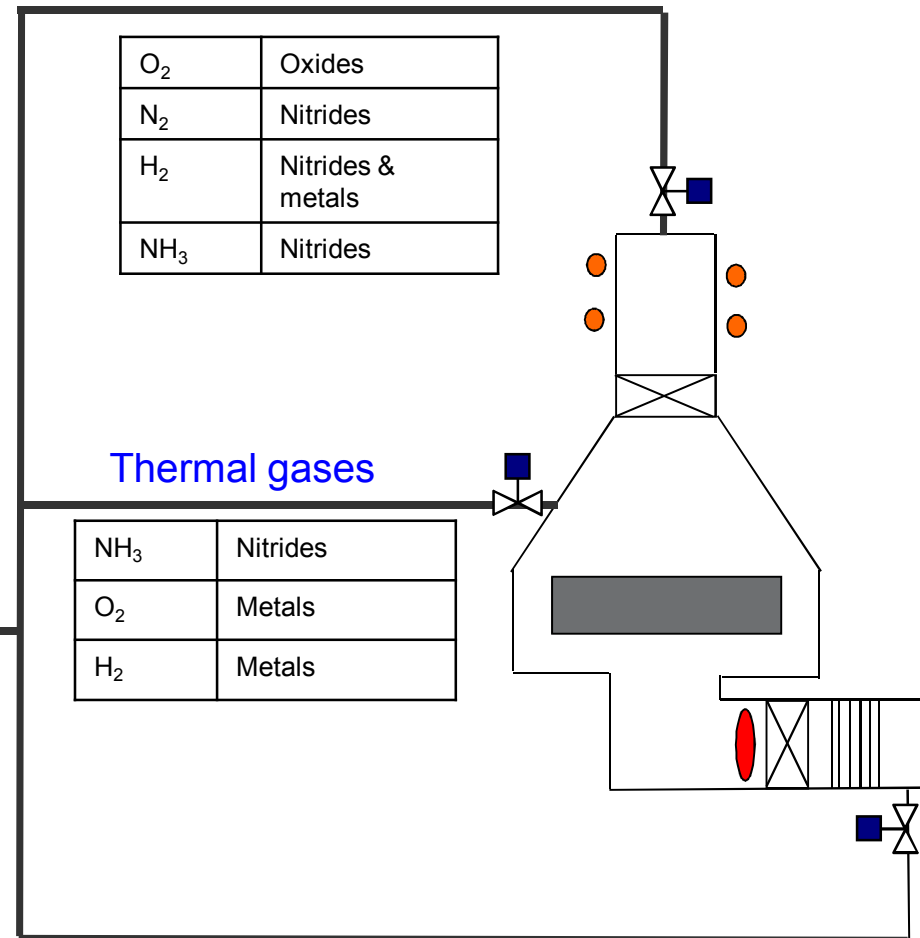


Plasma gases

O ₂	Oxides
N ₂	Nitrides
H ₂	Nitrides & metals
NH ₃	Nitrides

Thermal gases

NH ₃	Nitrides
O ₂	Metals
H ₂	Metals



- Extensive process library
- Rapidly growing
- Free of charge access to library for lifetime of tool

Oxides	Metals	Nitrides	Precursor
Al ₂ O ₃	Al	AlN	TMA
HfO ₂	Hf	HfN *	TEMAH
PtO ₂ *	Pt		Me ₃ Pt(MeCp)
	Ru		Ru(EtCp) ₂
SiO ₂	Si	Si ₃ N ₄	BDEAS/3DMAS/BTBAS
Ta ₂ O ₅	Ta	TaN	TBTDMT
TiO ₂	Ti	TiN	TDMAT / TTIP / TiCl ₄
SrTiO ₃ *			Sr(<i>i</i> Pr ₃ Cp) ₂ DME + TiO ₂ prec.
WO _x *	W	WN	WNBURE
ZnO	Zn		DEZ
In ₂ O ₃ *			InCp
	Nb	NbN *	TBTDEN / TBTMEN
Co ₃ O ₄ *	Co		CoCp ₂
Gd ₂ O ₃ *	Gd	GdN *	Gd(<i>i</i> PrCp) ₃ / Gd(MeCp) ₃
ZrO ₂ *	Zr		(MeCp) ₂ Zr(OMe)(Me)
	Ga	GaN	TEG

* Knowledge from customer base

Element for reference only

Materials possible by ALD (literature)

H

He

Deposited by ALD

Blue: compound with element

Gray: 2nd element in compound

Underline: pure element

Red circle: nitride

Li	Be											<u>B</u>	<u>C</u>	N	O	F	Ne
Na	Mg											<u>Al</u>	<u>Si</u>	P	S	Cl	Ar
K	Ca	Sc	<u>Ti</u>	<u>V</u>	Cr	Mn	<u>Fe</u>	<u>Co</u>	<u>Ni</u>	<u>Cu</u>	<u>Zn</u>	<u>Ga</u>	<u>Ge</u>	As	Se	Br	Kr
Rb	Sr	Y	<u>Zr</u>	<u>Nb</u>	<u>Mo</u>	Tc	<u>Ru</u>	<u>Rh</u>	<u>Pd</u>	<u>Ag</u>	Cd	<u>In</u>	Sn	<u>Sb</u>	Te	I	Xe
Cs	Ba	*	<u>Hf</u>	<u>Ta</u>	<u>W</u>	Re	<u>Os</u>	<u>Ir</u>	<u>Pt</u>	<u>Au</u>	Hg	Tl	Pb	Bi	Po	At	Rn
Fr	Ra	**	Rf	Db	Sg	Bh	Hs	Mt	Ds	Rg	Cn	Uut	Fl	Uup	Lv	Uus	Uuo

*	La	Ce	Pr	Nd	Pm	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu
**	Ac	Th	Pa	U	Np	Pu	Am	Cm	Bk	Cf	Es	Fm	Md	No	Lr

Adapted from source by Eindhoven University of Technology, source: Miikkulainen et al., *J. Appl. Phys.* **113**, 021301 (2013).

